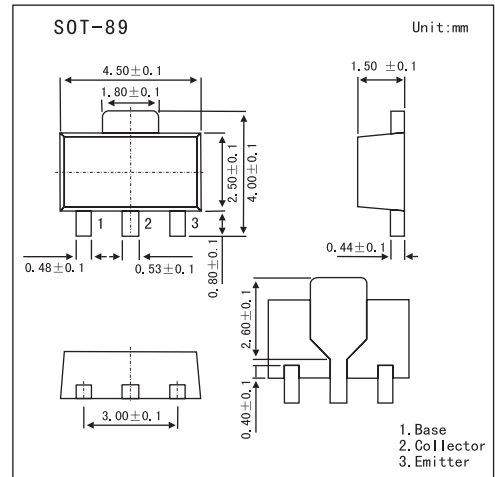


■ Features

- Low current (max. 50 mA)
- High voltage (max. 300 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
collector-base voltage (open emitter)	V <sub>CB0</sub>	300	V
		250	V
collector-emitter voltage (open-base)	V <sub>CE0</sub>	300	V
		250	V
emitter-base voltage (open collector)	V <sub>EB0</sub>	5	V
collector current (DC)	I <sub>c</sub>	50	mA
peak collector current	I <sub>CM</sub>	100	mA
peak base current	I <sub>BM</sub>	50	mA
total power dissipation T <sub>amb</sub> ≤ 25 °C *	P <sub>tot</sub>	1.25	W
storage temperature	T <sub>stg</sub>	-65 to 150	°C
junction temperature	T <sub>j</sub>	150	°C
operating ambient temperature	T <sub>amb</sub>	-65 to 150	°C
thermal resistance from junction to ambient *	R <sub>th j-a</sub>	100	K/W
thermal resistance from junction to soldering point	R <sub>th j-s</sub>	20	K/W

\* Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm<sup>2</sup>.

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$  unless otherwise specified.

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
collector cut-off current	$V_{(BR)CBO}$	$I_E = 0; V_{CB} = 200\text{ V}$			10	nA
		$I_E = 0; V_{CB} = 200\text{ V}; T_j = 150^\circ\text{C}$			10	mA
emitter cut-off current	$I_{EBO}$	$I_C = 0; V_{EB} = 5\text{ V}$			50	nA
DC current gain	$h_{FE}$	$I_C = 25\text{ mA}; V_{CE} = 20\text{ V}$	50			
collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 30\text{ mA}; I_B = 5\text{ mA}$			600	mV
feedback capacitance	$C_{re}$	$I_C = I_C = 0; V_{CE} = 30\text{ V}; f = 1\text{ MHz}$			1.6	pF
transition frequency	$f_T$	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	60			MHz

■ Marking

Type Number	BF620	BF622
Marking	DC	DA